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All Oxide Ferromagnet/Semiconductor Epitaxial Heterostructures

A. Nielsen,[1] A. Brandlmaier,[1] M. Althammer,[1] W. Kaiser,[1] M. Opel,[1]
J. Simon,[2] W. Mader,[2] S.T.B. Goennenwein,[1, 3] and R. Gross[1, 3, *]
[1] *Walther-Meißner-Institut, Bayerische Akademie der Wissenschaften, D-85748 Garching, Germany*
[2] *Institut für Anorganische Chemie, Universität Bonn, D-53117 Bonn, Germany*
[3] *Physik-Department, Technische Universität München, D-85748 Garching, Germany*

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Oxide based ferromagnet/semiconductor heterostructures offer substantial advantages for spin electronics. We have grown (111) oriented Fe_3O_4 thin films and Fe_3O_4/ZnO heterostructures on ZnO(0001) and Al_2O_3(0001) substrates by pulsed laser deposition. High quality crystalline films with mosaic spread as small as 0.03°, sharp interfaces, and rms surface roughness of 0.3 nm were achieved. Magnetization measurements show clear ferromagnetic behavior of the magnetite layers with a saturation magnetization of $3.2\,\mu_B$/f.u. at 300 K. Our results demonstrate that the Fe_3O_4/ZnO system is an intriguing and promising candidate for the realization of multi-functional heterostructures.

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In spin electronics the spin degree of freedom is exploited to realize electronic devices with novel or superior functionality [1, 2]. For *semiconductor* spintronic devices, charge carrier populations with a controllable spin polarization must be created within conventional semiconductors. A seemingly straightforward approach to do so is to inject spin polarized carriers from a ferromagnetic electrode into the semiconductor material. Unfortunately, the large conductivity mismatch between conventional metallic 3d ferromagnets and semiconductors prevents an efficient spin injection [3]. This problem can be circumvented e.g. via the introduction of Schottky or tunnel barriers at the ferromagnet/semiconductor (FM/SC) interface [4]. An alternative approach is to use ferromagnetic materials with very high spin polarization and small conductivity mismatch with semiconductors. Ferromagnets with a spin polarization of 100% – so-called half metals – thus are most interesting. The oxide ferrimagnet Fe_3O_4, onto which we focus here, is a half metal according to band structure calculations [5], and a spin polarization of up to -(80 ± 5) % has been reported from spin-resolved photoelectron spectroscopy experiments in (111)-oriented Fe_3O_4 [6, 7]. Furthermore, the conductivity $\sigma \approx 200\,\Omega^{-1}\mathrm{cm}^{-1}$ of Fe_3O_4 at room temperature is low [8], while the Curie temperature $T_C \simeq 860\,\mathrm{K}$ is well above room temperature, making Fe_3O_4 a promising material for spin injection into semiconductors. However, the Fe_3O_4/semiconductor heterostructures investigated so far [9, 10, 11, 12, 13, 14] show that for both group IV and III-V semiconductors, it is very difficult to grow Fe_3O_4 thin films with high crystalline quality, while preventing the formation of secondary phases at the FM/SC interface. To our knowledge, the deposition of Fe_3O_4 onto a II-VI semiconductor has not been reported to date.

In this letter, we show that (111)-oriented Fe_3O_4 can be epitaxially grown onto the II-VI semiconductor ZnO using pulsed laser deposition (PLD). Furthermore, we demonstrate the epitaxial growth of ZnO thin films onto (111)-oriented Fe_3O_4. The FM/SC heterostructures thus obtained are characterized using x-ray diffraction (XRD), atomic force microscopy (AFM), transmission electron microscopy (TEM), and superconducting quantum interference device (SQUID) magnetometry. Our results are compared to the properties of (111)-oriented Fe_3O_4 films on Al_2O_3 substrates, which have been extensively investigated and can be considered as a benchmark system [15, 16, 17, 18, 19, 20]. We find that the magnetic and structural properties of our (111) Fe_3O_4 films on ZnO are state of the art, with sharp FM/SC interfaces. This makes them promising for spin injection devices.

We have grown four different types of epitaxial Fe_3O_4-based thin film samples by pulsed laser deposition [21]: (i) single Fe_3O_4 layers, deposited on ZnO(0001) substrates, (ii) single Fe_3O_4 layers on Al_2O_3(0001) substrates, (iii) ZnO/Fe_3O_4 thin film heterostructures on ZnO(0001), and (iv) ZnO/Fe_3O_4 heterostructures on Al_2O_3(0001). In the following, we will refer to these samples as Fe_3O_4//ZnO, Fe_3O_4//Al_2O_3, ZnO/Fe_3O_4//ZnO, and ZnO/Fe_3O_4//Al_2O_3, respectively. Both the Fe_3O_4 and the ZnO layers were deposited from stoichiometric Fe_3O_4 and ZnO targets, respectively, using identical growth parameters. All samples were grown in pure Ar atmosphere at a pressure of 3.7×10^{-3} mbar and a substrate temperature of 590 K. The energy density of the KrF excimer laser pulses (wavelength $\lambda = 248\,\mathrm{nm}$) on the respective targets was $2\,\mathrm{J/cm^2}$ at a pulse repetition rate of 2 Hz.

We first address the structural and magnetic properties of the Fe_3O_4//ZnO and Fe_3O_4//Al_2O_3 single layer films. Figure 1 shows representative ω-2θ scans of all four sample types. Set aside the substrate reflections, only $Fe_3O_4(\ell\ell\ell)$ and ZnO(000ℓ) reflections are observed. This shows that magnetite grows (111)-oriented on ZnO

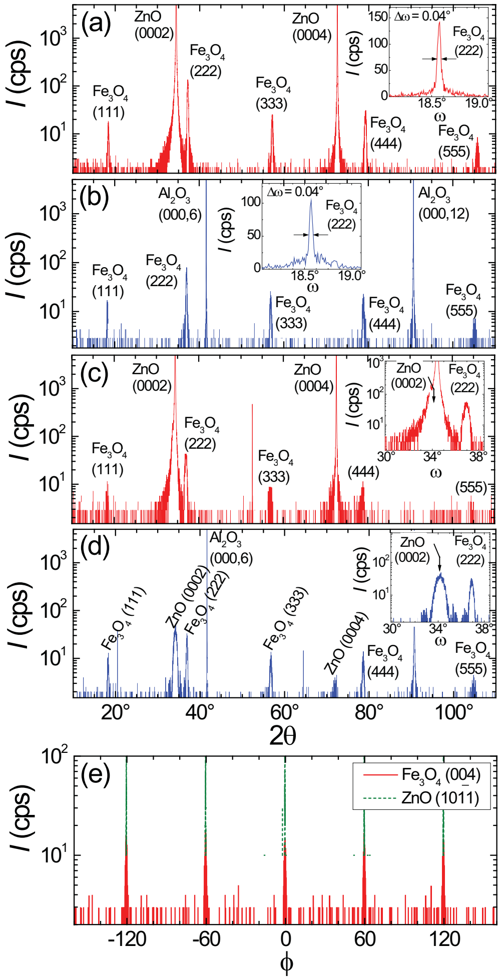

FIG. 1: ω-2θ scans of a 31 nm thick $Fe_3O_4(111)$ film on ZnO(0001) (a), a 34 nm thick $Fe_3O_4(111)$ film on $Al_2O_3(0001)$ (b), a ZnO/Fe_3O_4//ZnO (29 nm/18 nm) heterostructure (c), and a ZnO/Fe_3O_4//Al_2O_3 (11 nm/28 nm) heterostructure (d). In (e) ϕ scans of the Fe_3O_4 (004) and the ZnO $(10\bar{1}1)$ reflections of the Fe_3O_4 film on ZnO (cf. panel (b)) are shown.

(0001) substrates, in close analogy to films on Al_2O_3 (0001) substrates [18]. Furthermore, in the ZnO/Fe_3O_4 heterostructures the ZnO layer grows (0001) oriented on the (111) oriented Fe_3O_4 layer. The fact that Fe_3O_4 grows on both substrates in (111) orientation is astonishing. Bulk Fe_3O_4 showing the inverse spinel structure ($Fd3m$) is cubic with lattice constant of $a_{Fe_3O_4} = 8.3963\,\text{Å}$ [22]. ZnO has hexagonal wurzite structure with $a_{ZnO} = 3.2498\,\text{Å}$ [23] and sapphire hexagonal structure ($R\bar{3}c$) with $a_{Al_2O_3} = 4.759\,\text{Å}$ in the hexagonal cell [24]. Therefore, there is a large lattice mismatch between multiples of the a-axis lattice parameters of both substrates and $\sqrt{2}a$ for the (111) oriented Fe_3O_4. The same is true for other Fe_3O_4 orientations. Nevertheless, Fe_3O_4 tends to grow in (111) orientation with well defined epitaxial relations on substrates which are not well lattice matched [9, 13]. To quantify the Fe_3O_4 lattice parameters, the (111) lattice plane distance d_{111} was evaluated. For Fe_3O_4//ZnO samples, this leads to $d_{111} = (4.836 \pm 0.005)\,\text{Å}$, and for Fe_3O_4//Al_2O_3 we obtain $d_{111} = (4.852 \pm 0.005)\,\text{Å}$. These values are close to $d_{111,\text{bulk}} = 4.848\text{Å}$ of bulk Fe_3O_4 [22], suggesting that the films grow fully relaxed. Small deviations of the film d_{111} from $d_{111,\text{bulk}}$ have been reported for growth on Si, GaAs, Al_2O_3, and are attributed to substrate-induced strain. The in-plane epitaxial relations between the Fe_3O_4 film and the substrates have been derived from ϕ-scans. For Fe_3O_4//ZnO, the $\{004\}$ reflections of magnetite appears every 60° at the same ϕ angles as the ZnO $\{10\bar{1}1\}$ reflection (Fig. 1(e)). This demonstrates the good in-plane orientation of $Fe_3O_4(111)$ films on ZnO, with the ZnO $[2\bar{1}\bar{1}0]$ close-packed direction parallel to the Fe_3O_4 $[1\bar{1}0]$ close-packed direction. The same parallelism of the close-packed oxygen sub-lattices is obtained for the epitaxial Fe_3O_4//Al_2O_3 film. The good structural quality of the samples is further evidenced by the small full width at half maximum (FWHM) of the (222) (out of plane) rocking curve $\Delta\omega = 0.04°$ in both Fe_3O_4//ZnO and Fe_3O_4//Al_2O_3. Within the film plane, the mosaicity is somewhat larger, with $\Delta\omega \simeq 0.9°$ for the (004) Fe_3O_4 reflection in Fe_3O_4//ZnO. The surface roughness of the films was studied using atomic force microscopy at room temperature. For the Fe_3O_4//ZnO sample, a rms roughness of 0.3 nm is found, with a peak to peak value of 0.8 nm in an area of $0.9 \times 0.9\,\mu\text{m}^2$ (not shown). This low surface roughness is an important prerequisite for the realization of Fe_3O_4/ZnO FM/SC heterostructures with smooth interfaces.

The magnetic properties of the Fe_3O_4 thin films were investigated using a SQUID magnetometer. Figure 2 shows the magnetization M versus magnetic field H of the Fe_3O_4//ZnO and Fe_3O_4//Al_2O_3 samples discussed above (cf. Fig. 1). The diamagnetic contribution of the substrates has been subtracted. The magnetic hysteresis loops of both films show clear ferromagnetic hys-

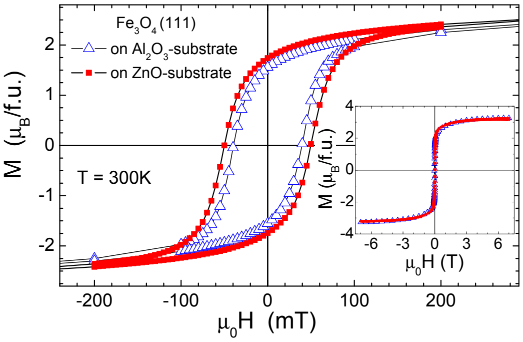

FIG. 2: $M(H)$ curves of Fe_3O_4 films grown on (a) Al_2O_3 (open triangles, 34 nm thick) and (b) ZnO (full squares, 31 nm thick), taken at 300 K with $H \| [1\bar{1}0]$ of Fe_3O_4. The inset shows the same data on an enlarged field scale.

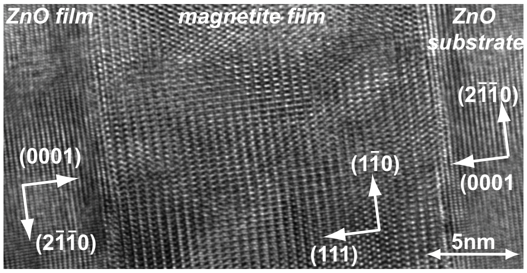

FIG. 3: HRTEM image of an 18 nm thick (111) oriented Fe_3O_4 film on a (0001) ZnO substrate (right) with a 29 nm thick (000$\bar{1}$) oriented ZnO film on top (left).

teresis. The coercivity $\mu_0 H_c = 50\,mT$ and the remanence $M_R = 1.74\,\mu_B$/f.u. for Fe_3O_4//ZnO are closely comparable to $\mu_0 H_c = 40\,mT$ and $M_R = 1.55\,\mu_B$/f.u. for Fe_3O_4//Al_2O_3. Note that these coercive fields are well within the range $30\,mT \leq \mu_0 H_c \leq 60\,mT$ reported for (111) oriented Fe_3O_4 films grown on sapphire [15, 18, 19, 20]. At $\mu_0 H = 7\,T$, the magnetization reaches $3.2\,\mu_B$/f.u. in both films (Fig. 2, inset), but does not fully saturate. This most likely originates from the presence of antiphase boundaries [16, 20]. Taken together, the magnetometry results show that the (111)-oriented Fe_3O_4 thin films grown on ZnO can be considered as state of the art also in terms of their magnetic properties.

Having established that (111) oriented Fe_3O_4 thin films with excellent structural, magnetic, and surface properties can be grown on ZnO(0001) substrates, we further demonstrate that it is also possible to grow ZnO films epitaxially onto (111)-oriented Fe_3O_4. In this way fully epitaxial Fe_3O_4/ZnO heterostructures can be realized. Figure 1(c) and (d) show ω-2θ x-ray diffraction scans of representative ZnO/Fe_3O_4//ZnO and ZnO/Fe_3O_4//Al_2O_3 samples. For the ZnO/Fe_3O_4//Al_2O_3 sample, the (000ℓ) ZnO film reflections are not masked by the substrate reflections and can thus be unambiguously identified. Instead of going through the details of the structural and magnetic characterization once more, let us note that the structural quality of the heterostructure samples again is very good, matching the crystalline properties of the single Fe_3O_4 layers discussed above. In the following we will discuss the results of the TEM analysis. Figure 3 shows a TEM cross-sectional micrograph of the ZnO/Fe_3O_4//ZnO sample. Electron diffraction shows that the ZnO film is (000$\bar{1}$) oriented, whereas the ZnO substrate is (0001) oriented. Hence, the *c* axes of the polar ZnO crystals of both substrate and film point towards the magnetite film which is important for a stable interface and which can be explained by arguments of structural chemistry. Smooth and abrupt interfaces between the ZnO and Fe_3O_4 layers are clearly evident from Fig. 3, corroborating the conclusions drawn from the XRD analysis.

In summary, we have grown Fe_3O_4(111) films and fully epitaxial ZnO(0001)/Fe_3O_4(111) heterostructures on (0001)-oriented ZnO and Al_2O_3 substrates. While the deposition of Fe_3O_4 on Al_2O_3 is established, the growth of Fe_3O_4/ZnO FM/SC heterostructures has not yet been explored to our knowledge. Combining XRD, AFM, TEM, and SQUID magnetometry, we show that the Fe_3O_4 films are state of the art in terms of their structural and magnetic properties, with smooth and abrupt interfaces between Fe_3O_4 and ZnO. This suggests that the Fe_3O_4/ZnO system is an interesting and promising material combination for the realization of multifunctional FM/SC heterostructures.

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[*] Electronic address: Rudolf.Gross@wmi.badw.de

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